



Product Overview

NTGD4161P: Power MOSFET -30V -2.3A 160 mOhm Dual P-Channel TSOP6

For complete documentation, see the data sheet

Product Description

Power MOSFET -30 V, -2.3 A, Dual P-Channel, TSOP-6

Features

- Fast Switching Speed
- Low Gate Charge
- Low $R_{DS(on)}$
- Independently Connected Devices to Provide Design Flexibility
- This is a Pb-Free Device

Applications

- Load Switch
- Battery Protection
- Portable Devices Like PDAs, Cellular Phones and Hard Drives

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{DS}^{(BR)}$ Min (V)	$V_{GS}^{(th)}$ Max (V)	$V_{GS}^{(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$r_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 10$ V (m)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	Q_{gd} Typ @ $V_{GS} = 4.5$ V (nC)	Q_{rr} Typ (nC)	C_{iss} Typ (pF)	C_{oss} Typ (pF)	C_{rss} Typ (pF)	Package Type
NTGD4161PT1G	Pb-free Halide free	Active	P-Channel	Dual	30	20	3	2.3	1.3			160		7.1		3	281	50	28	TSOP-6

For more information please contact your local sales support at www.onsemi.com

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